

1200V N-Channel Silicon Carbide Power MOSFET

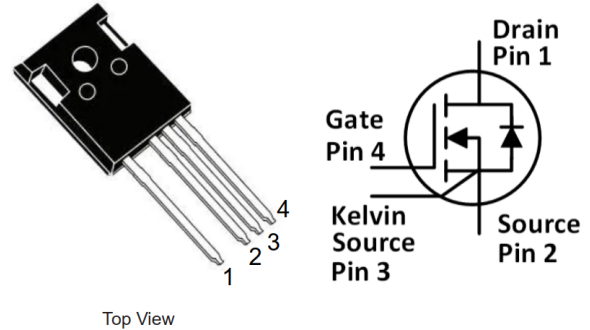
Features:

- High blocking voltage with low on-resistance
- High speed switching with low capacitance
- High operating junction temperature capability
- Very fast and robust intrinsic body diode
- Kelvin gate input easing driver circuit design

Applications:

- Solar inverters
- UPS
- Motor drivers
- High voltage DC/DC converters
- Switch mode power supplies

Package:



Part Number	Package
DTN20N120SC4	TO247-4

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DS}	Drain-Source voltage	1200	V	$V_{GS}=0\text{V}$, $I_D=100\mu\text{A}$	
V_{GS}	Gate-Source voltage	-5 to 20	V	Recommended maximum	
I_D	Drain current (continuous)	20	A	$V_{GS}=20\text{V}$, $T_c=25^\circ\text{C}$	Fig. 21
		16	A	$V_{GS}=20\text{V}$, $T_c=100^\circ\text{C}$	
I_{DM}	Drain current (pulsed)	50	A	Pulse width limited by SOA	Fig. 24
P_{TOT}	Total power dissipation	138	W	$T_c=25^\circ\text{C}$	Fig. 22
T_{stg}	Storage temperature range	-55 to 175	$^\circ\text{C}$		
T_J	Operating junction temperature	-55 to 175	$^\circ\text{C}$		
T_L	Solder Temperature	260	$^\circ\text{C}$	Wave soldering only allowed at leads, 1.6mm from case for 10 s	

Thermal Data

Symbol	Parameter	Value	Unit	Note
$R_{\theta(j-c)}$	Thermal Resistance from Junction to Case	1.088	$^\circ\text{C}/\text{W}$	Fig. 23

Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
I_{DSS}	Zero gate voltage drain current		5	100	μA	$V_{DS}=1200\text{V}, V_{GS}=0\text{V}$	
I_{GSS}	Gate leakage current		1	± 100	nA	$V_{DS}=0\text{V}, V_{GS}=-5\sim 20\text{V}$	
V_{TH}	Gate threshold voltage		2.9		V	$V_{GS}=V_{DS}, I_D=1.9\text{mA}$	Fig. 8, 9
			1.9			$V_{GS}=V_{DS}, I_D=1.9\text{mA}$ @ $T_c=175^\circ\text{C}$	
R_{ON}	Static drain-source on-resistance		160	195	$\text{m}\Omega$	$V_{GS}=20\text{V}, I_D=10\text{A}$ @ $T_j=25^\circ\text{C}$	Fig. 4, 5, 6, 7
			250		$\text{m}\Omega$	$V_{GS}=20\text{V}, I_D=10\text{A}$ @ $T_j=175^\circ\text{C}$	
C_{iss}	Input capacitance		885		pF	$V_{DS}=800\text{V}, V_{GS}=0\text{V},$ $f=1\text{MHz}, V_{AC}=25\text{mV}$	Fig. 16
C_{oss}	Output capacitance		38		pF		
C_{rss}	Reverse transfer capacitance		2		pF		
E_{oss}	C_{oss} stored energy		16		μJ		Fig. 17
Q_g	Total gate charge		43		nC	$V_{DS}=800\text{V}, I_D=10\text{A},$ $V_{GS}=-5\text{ to }20\text{V}$	Fig. 18
Q_{gs}	Gate-source charge		9		nC		
Q_{gd}	Gate-drain charge		19		nC		
R_g	Gate input resistance		9.5		Ω	$f=1\text{MHz}$	
E_{ON}	Turn-on switching energy		139.3		μJ	$V_{DS}=800\text{V}, I_D=10\text{A},$ $V_{GS}=-2\text{ to }20\text{V},$ $R_{G(\text{ext})}=5.1\Omega,$ $L=450\mu\text{H}$	Fig. 19, 20
E_{OFF}	Turn-off switching energy		39.2		μJ		
$t_{d(\text{on})}$	Turn-on delay time		6.4		ns		
t_r	Rise time		19.4				
$t_{d(\text{off})}$	Turn-off delay time		11.8				
t_f	Fall time		14				

Reverse Diode Characteristics ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
V_{SD}	Diode forward voltage		4.1		V	$I_{SD}=5\text{A}, V_{GS}=0\text{V}$	Fig. 10, 11, 12
			3.7		V	$I_{SD}=5\text{A}, V_{GS}=0\text{V},$ $T_J=175^\circ\text{C}$	
t_{rr}	Reverse recovery time		33.2		ns	$V_{GS}=-2\text{V}/+20\text{V},$ $I_{SD}=10\text{A}, V_R=800\text{V},$ $di/dt=1000\text{A}/\mu\text{s},$	
Q_{rr}	Reverse recovery charge		101.5		nC		
I_{RRM}	Peak reverse recovery current		5.6		A	$R_{G(ext)}=13.0\Omega$	

Typical Performance (curves)

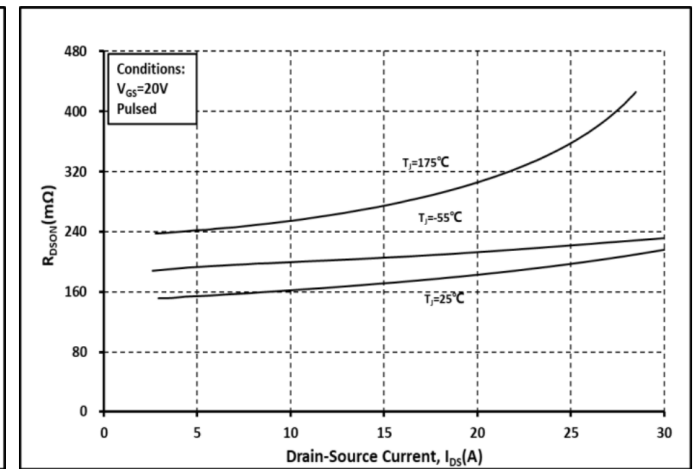
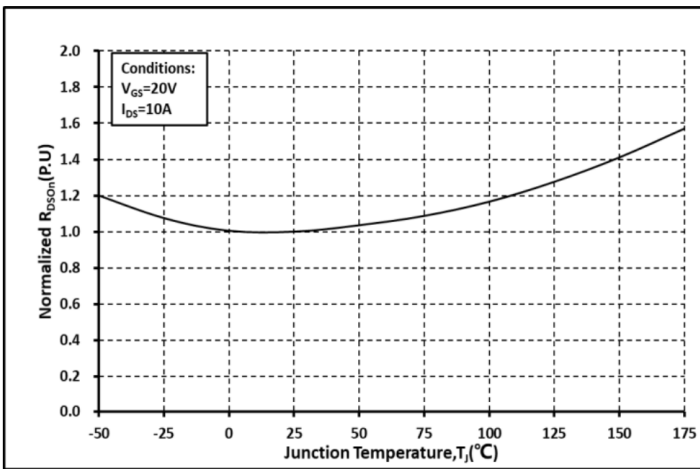
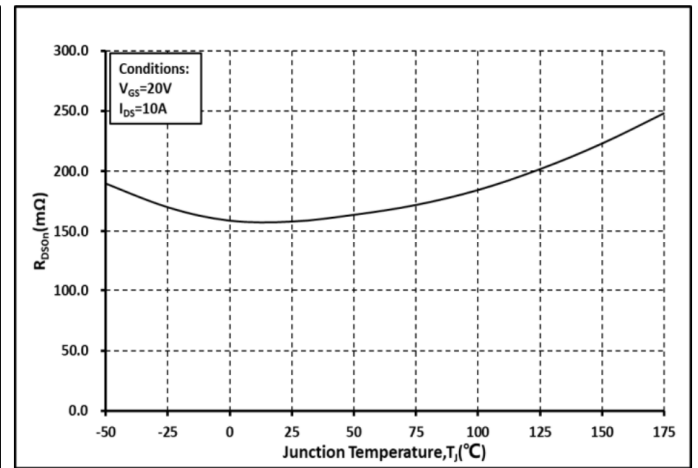
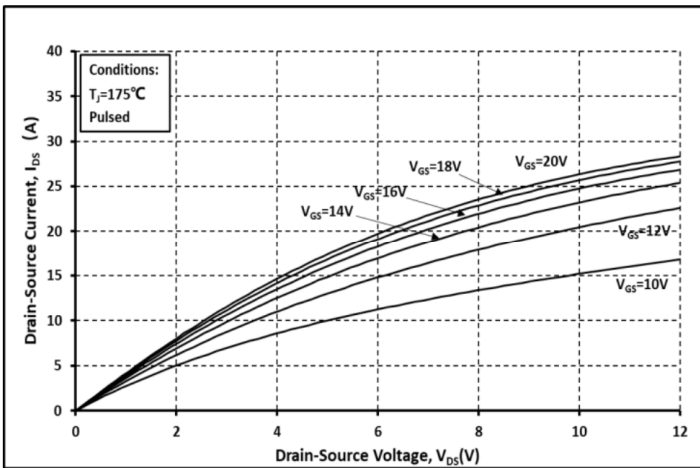
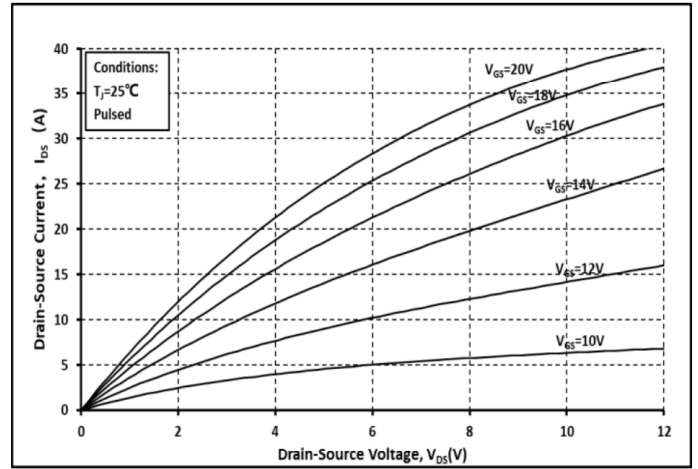
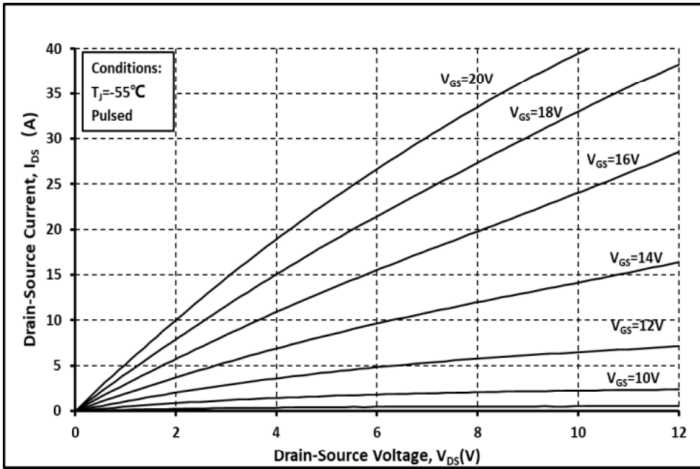


Fig. 5 Normalized $R_{ds(on)}$ vs. Temperature

Fig. 6 $R_{ds(on)}$ vs. I_{ds} @ Various Temperature

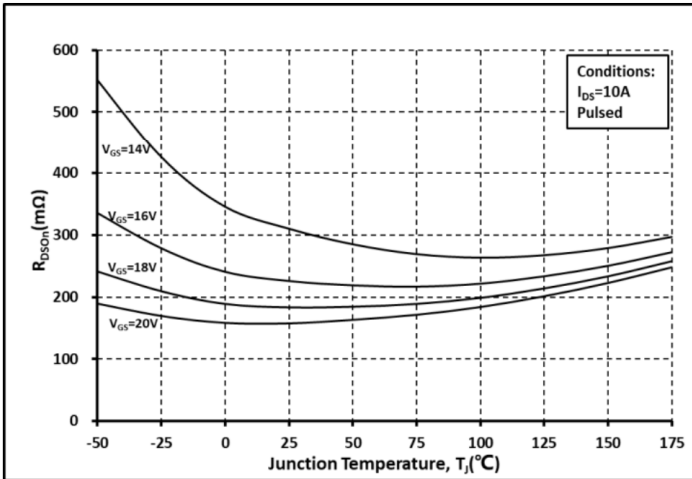


Fig. 7 Ron vs. Temperature @ Various V_{GS}

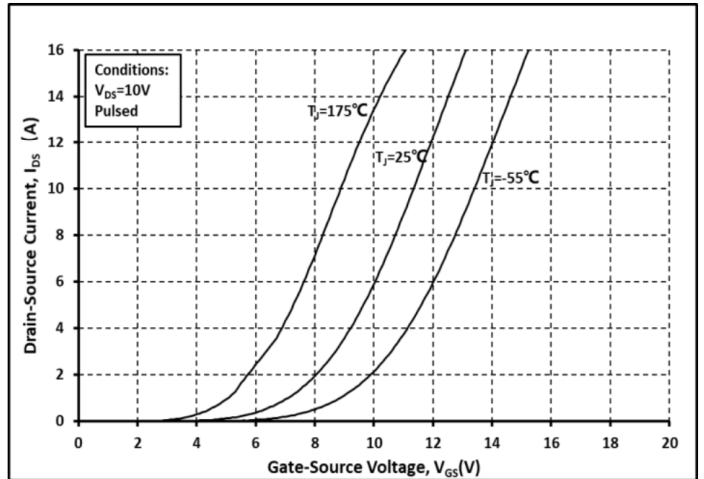


Fig. 8 Transfer Curves @ Various Temperature

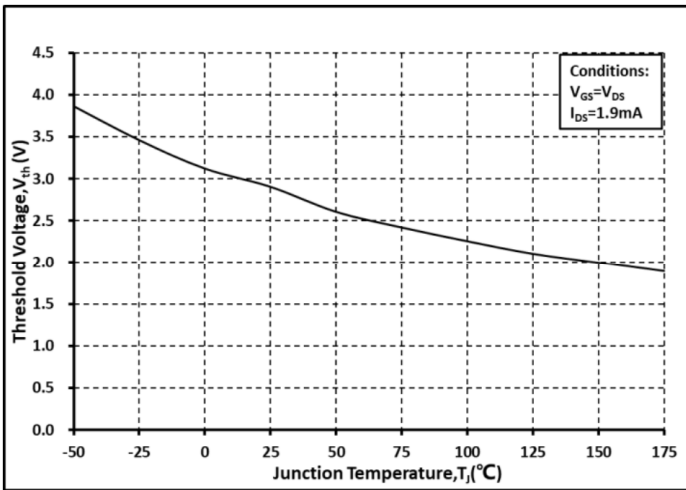


Fig. 9 Threshold Voltage vs. Temperature

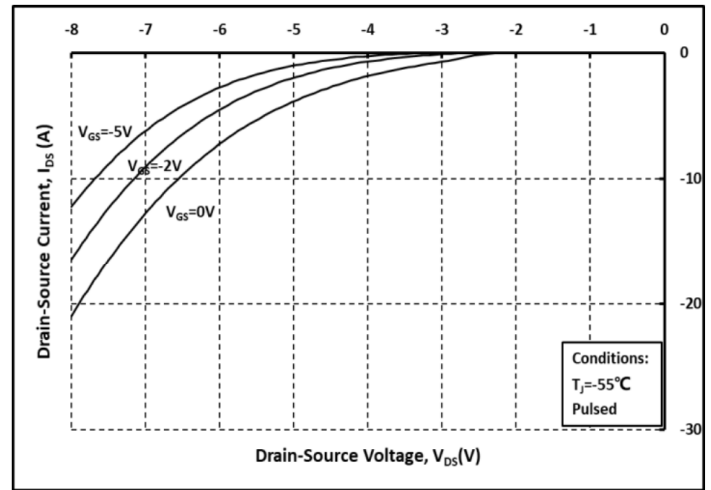


Fig. 10 Body Diode Curves @ $T_j = -55^\circ\text{C}$

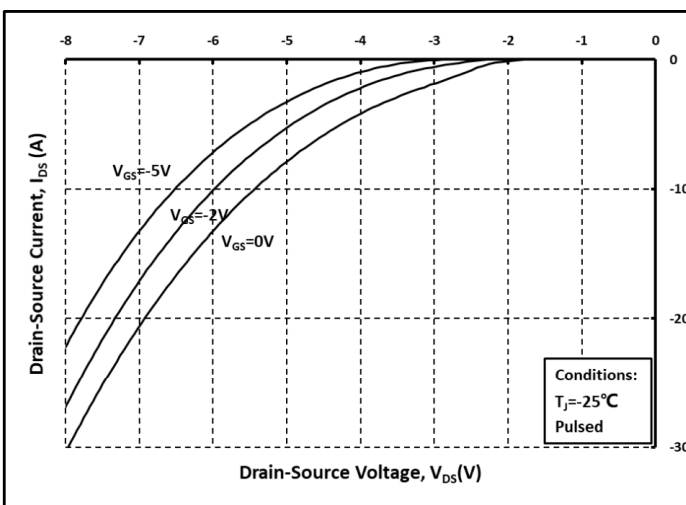


Fig. 11 Body Diode Curves @ $T_j = 25^\circ\text{C}$

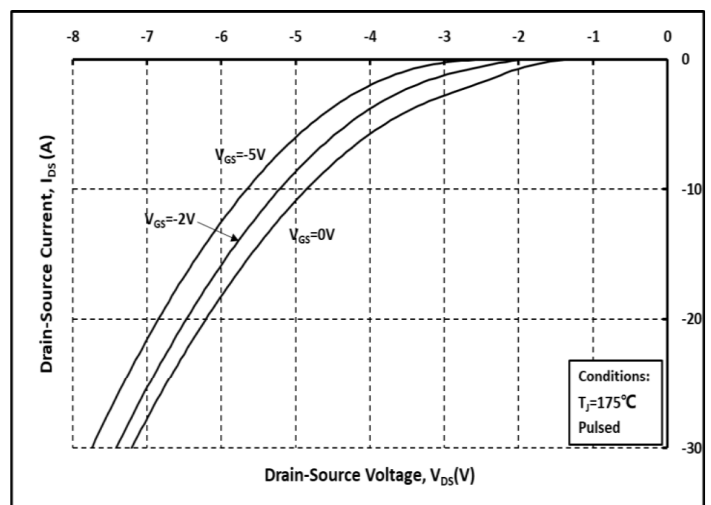


Fig. 12 Body Diode Curves @ $T_j = 175^\circ\text{C}$

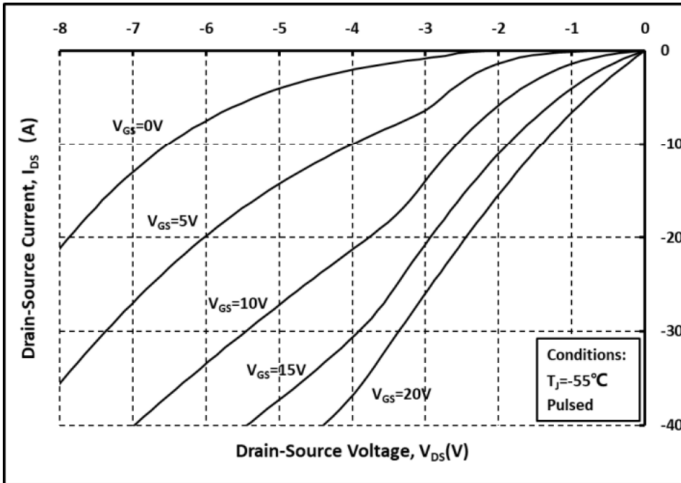


Fig. 13 3rd Quadrant Curves @ $T_j = -55^\circ\text{C}$

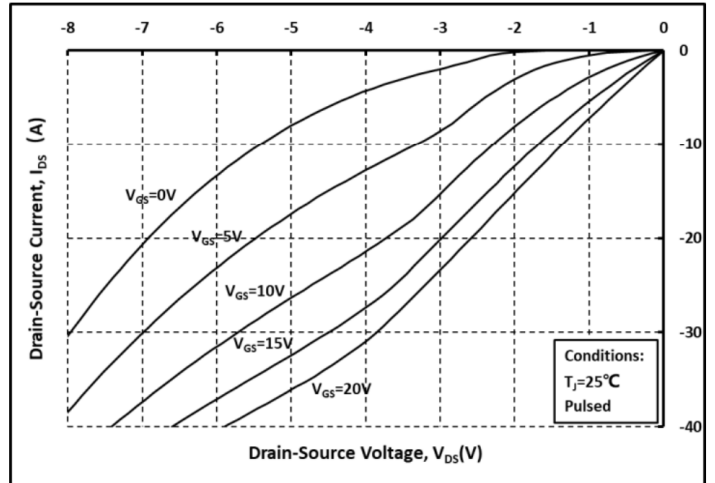


Fig. 14 3rd Quadrant Curves @ $T_j = 25^\circ\text{C}$

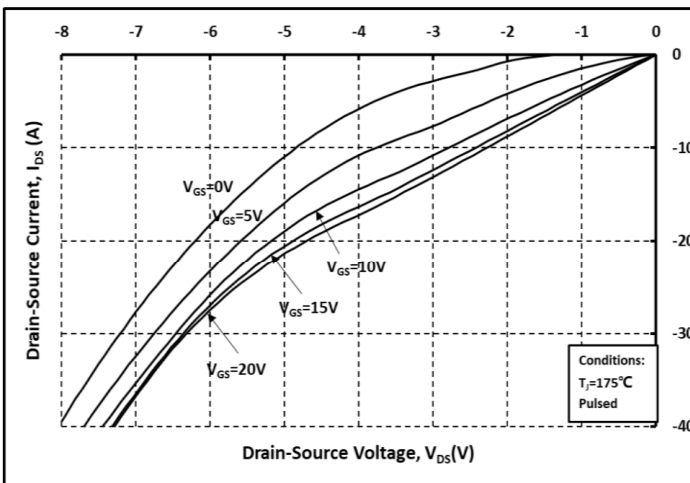


Fig. 15 3rd Quadrant Curves @ $T_j = 175^\circ\text{C}$

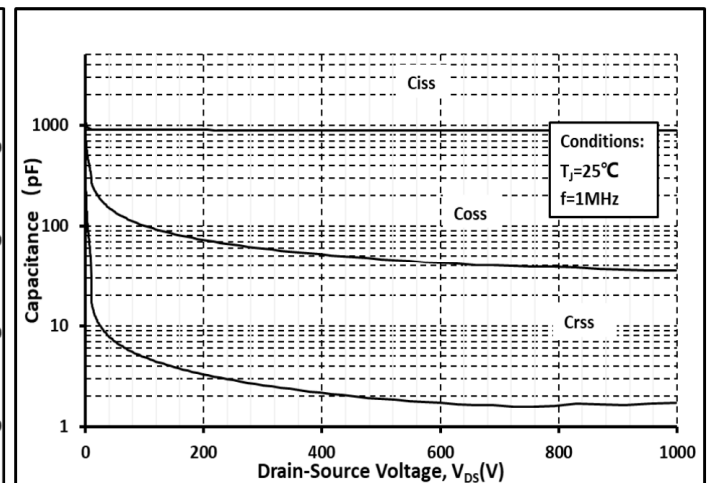


Fig. 16 Capacitance vs. V_{DS}

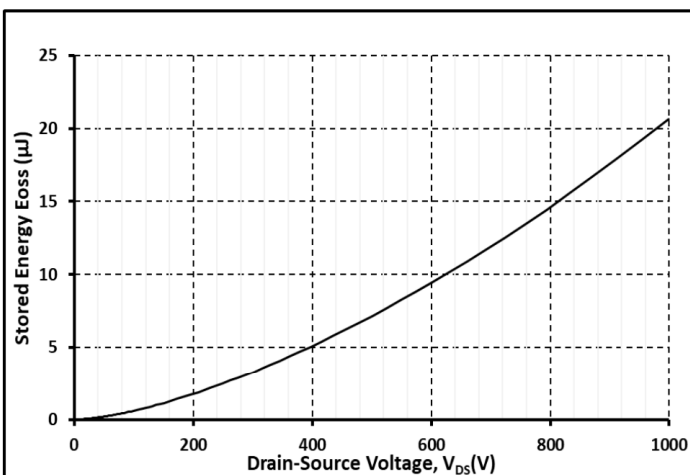


Fig. 17 Output Capacitor Stored Energy

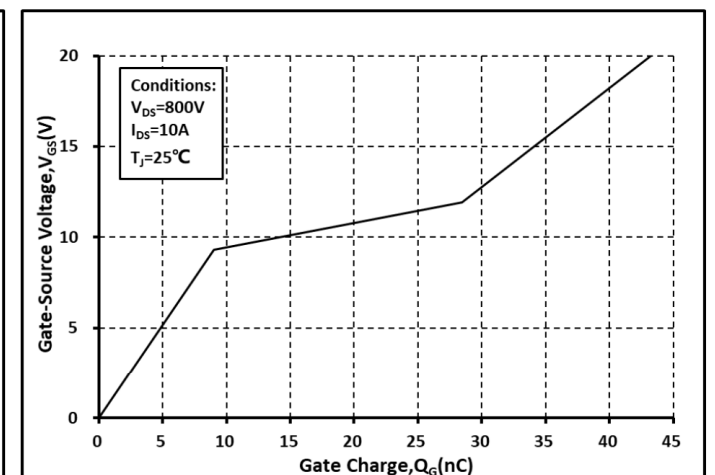


Fig. 18 Gate Charge Characteristics

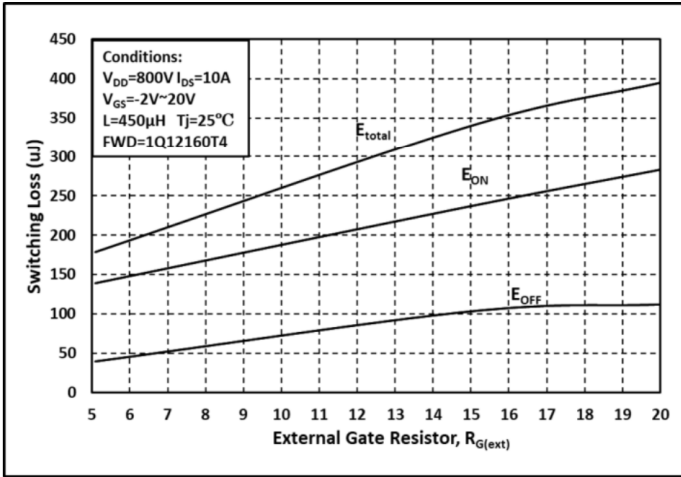


Fig. 19 Switching Energy vs. $R_{G(ext)}$

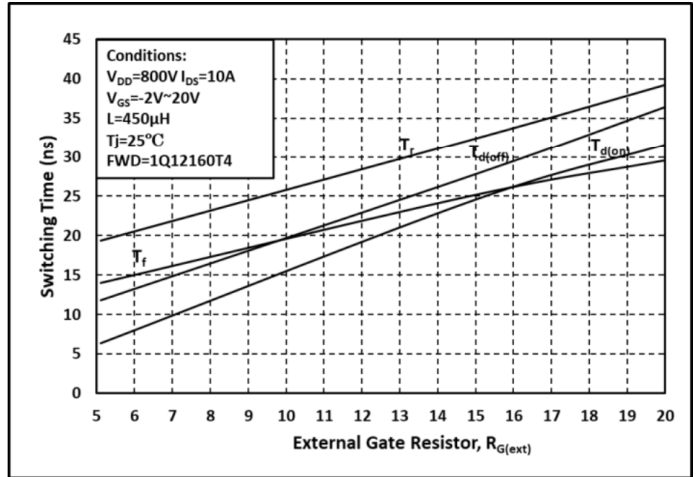


Fig. 20 Switching Times vs. $R_{G(ext)}$

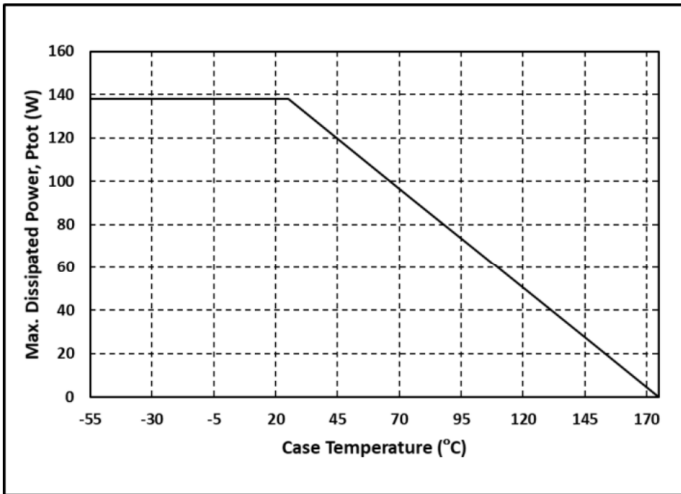


Fig. 21 Continuous Drain Current vs. Case Temperature

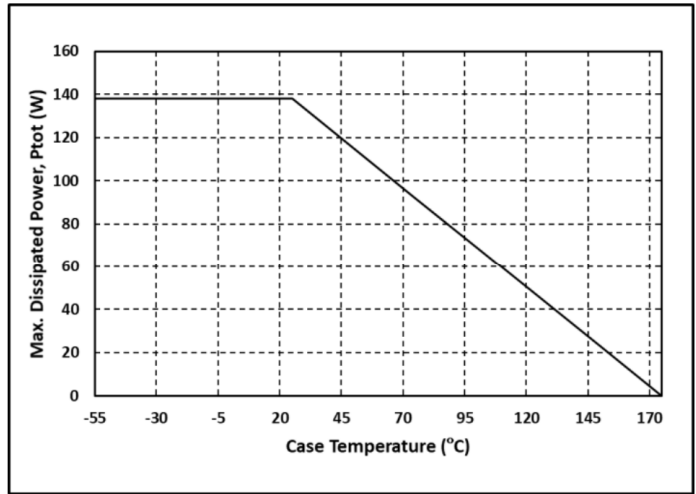


Fig. 22 Max. Power Dissipation Derating vs. Case Temperature

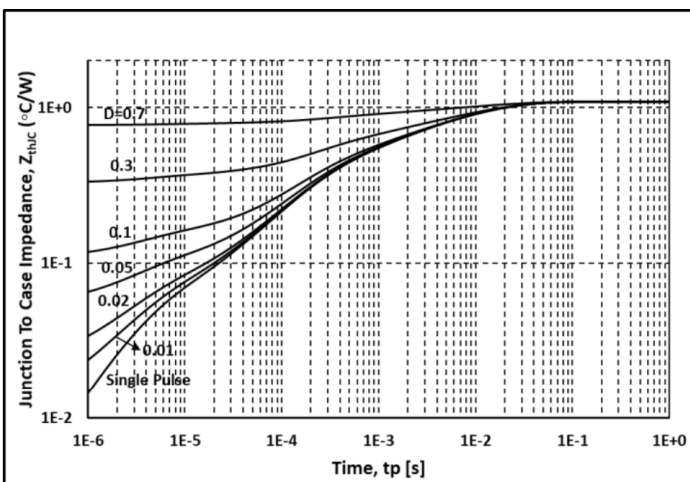


Fig. 23 Thermal Impedance

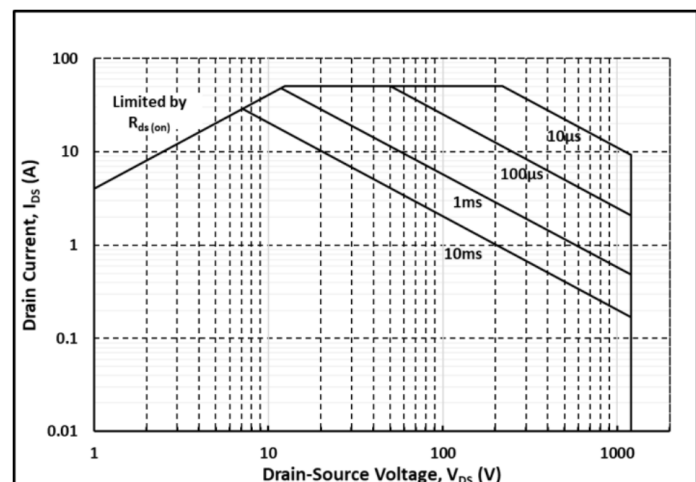
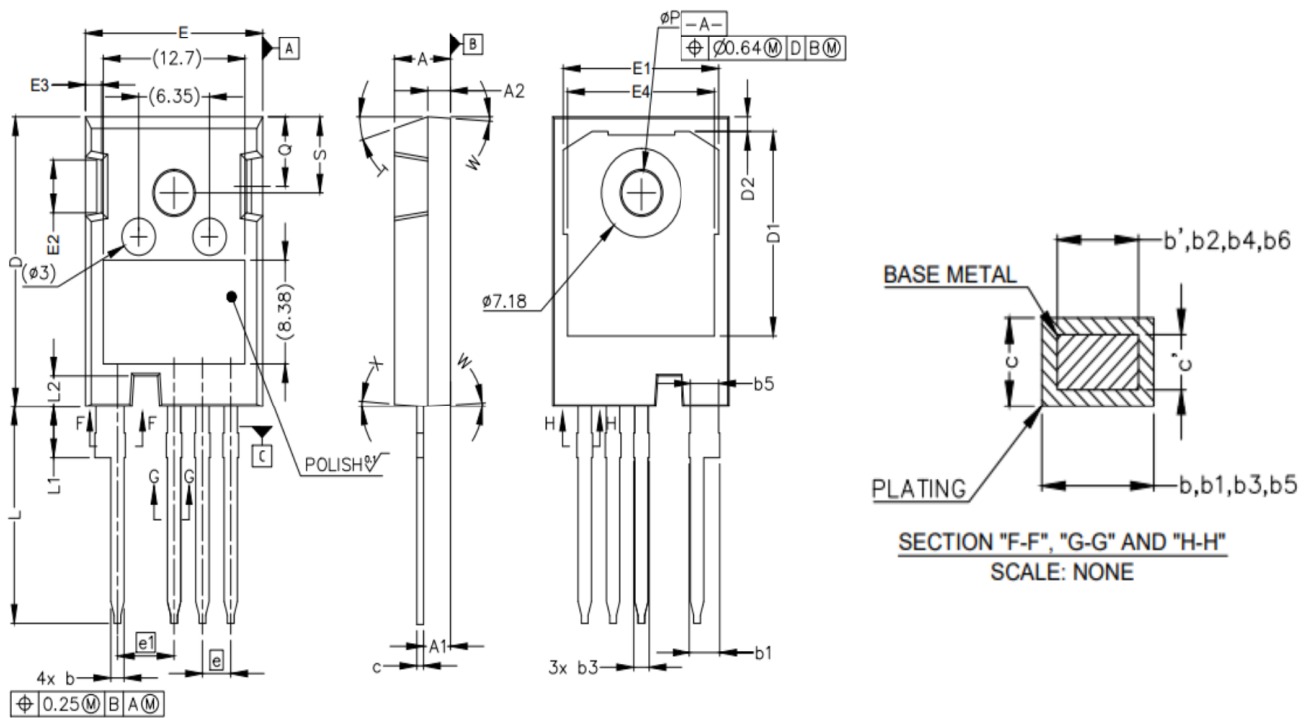


Fig. 24 Safe Operating Area

TO-247_4L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	TYP	MAX	SYMBOL	MIN	TYP	MAX
A	4.50	5.02	5.50	E1	12.50	14.02	15.00
A1	2.00	2.40	2.80	E2	3.00	4.40	5.00
A2	1.80	2.00	2.30	E3	0.80	1.45	2.10
b'	0.90	1.20	1.40	E4	11.50	13.26	14.00
b	0.90	1.20	1.45	e	2.54BSC		
b1	2.15	2.67	3.10	e1	5.08BSC		
b2	2.15	2.67	3.05	N	4.00		
b3	0.90	1.30	1.80	L	16.00	17.57	19.00
b4	0.90	1.30	1.70	L1	3.47	4.19	4.87
b5	2.20	2.53	2.89	L2	2.05	2.50	2.95
b6	2.20	2.53	2.84	ΦP	3.21	3.61	3.95
c'	0.48	0.60	0.75	Q	5.09	5.79	6.40
c	0.48	0.60	0.78	S	5.74	6.21	6.60
D	22.50	23.45	24.50	T	17.5°REF		
D1	15.50	16.55	18.10	W	3.5°REF		
D2	0.85	1.19	1.35	X	4°REF		
E	15.00	15.94	17.00				

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